

N-Channel 120 V (D-S) 175 °C MOSFET

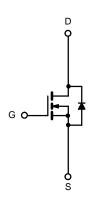
PRODUCT SUMMARY		
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)
120	0.0029 at V _{GS} = 10 V	188 ^a

FEATURES

- TrenchFET® Power MOSFET
- New Package with Low Thermal Resistance
- 100 % R_g Tested







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	120	V		
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current /T 475 °C)	T _C = 25 °C	I-	188 ^a	Α	
Continuous Drain Current (T _J = 175 °C)	T _C = 125 °C	· I _D	143 ^a		
Pulsed Drain Current	I _{DM}	650	A		
Avalanche Current		I _{AR}	180		
Repetitive Avalanche Energy ^b	L = 0.1 mH	E _{AR}	2200	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	В	398 ^c	W	
Maximum r ower bissipation	T _A = 25 °C	P_{D}	5.9	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Limit	Unit	
Junction-to-Ambient	PCB Mount (TO-263) ^d R _{thJA} 38		38	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/VV	

Notes:

- a. Package limited.

- a. Fackage liffilled.
 b. Duty cycle ≤ 1 %.
 c. See SOA curve for voltage derating.
 d. When mounted on 1" square PCB (FR-4 material).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	120			V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V			1	
	I _{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	μΑ
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	188			Α
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0029	0.0040	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.0053	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.0065	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	68			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 60 V, f = 1 MHz		8150		pF
Output Capacitance	C _{oss}			937		
Reverse Transfer Capacitance	C _{rss}			110		
Total Gate Charge ^c	Qg			110	150	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 60 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		46		
Gate-Drain Charge ^c	Q_{gd}			24		
Gate Resistance	R _g		1.0		6.3	Ω
Turn-On Delay Time ^c	t _{d(on)}			22	33	ns
Rise Time ^c	t _r	$V_{DD} = 60 \text{ V}, R_1 = 0.6 \Omega$		102	180	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		53	85	
Fall Time ^c	t _f			18	35	
Source-Drain Diode Ratings and Cha	aracteristics 7	T _C = 25 °C ^b				
Continuous Current	Is				188	۸
Pulsed Current	I _{SM}				650	Α
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}			55	149	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 20 A, dl/dt = 100 A/μs		5.3	10	Α
Reverse Recovery Charge	Q _{rr}			0.15	0.37	μС

Notes:

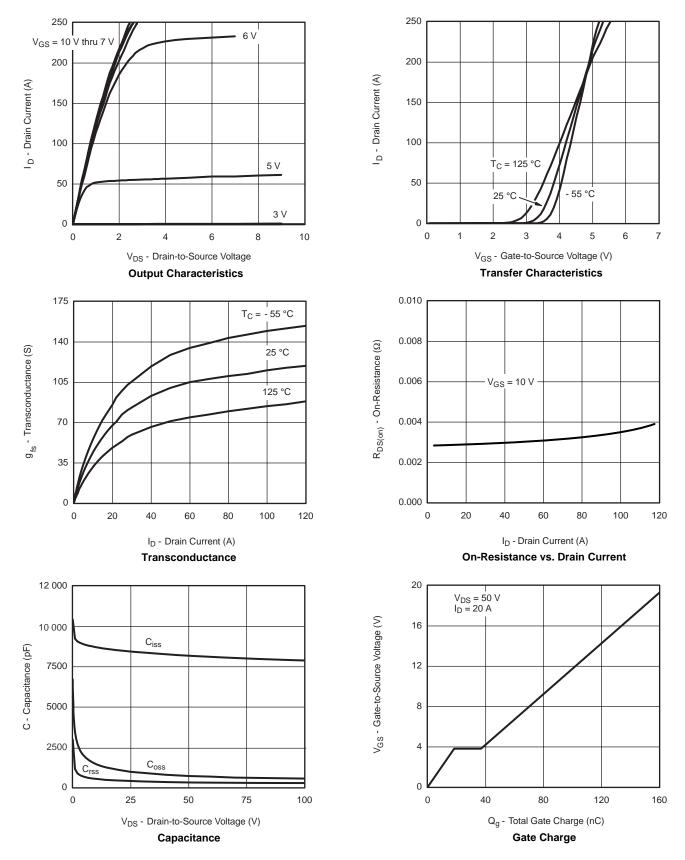
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





2000

200

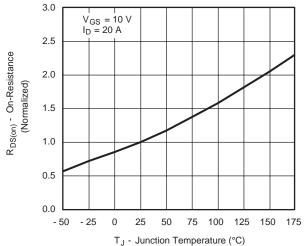
10

0.00001

I_{Dav} (A)

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





On-Resistance vs. Junction Temperature

 I_{AV} (A) at $T_A = 25$



 $\begin{array}{c} t_{\text{in}} \ \ (\text{s}) \\ \text{Avalanche Current vs. Time} \end{array}$

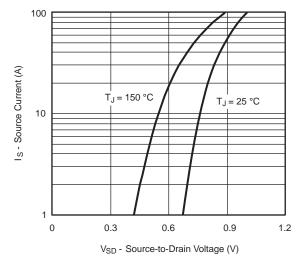
0.01

0.1

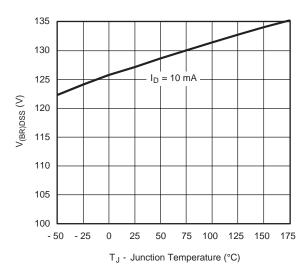
0.001

 I_{AV} (A) at T_A = 150 °C

0.0001



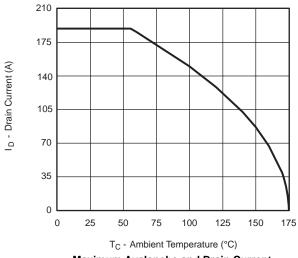
Source-Drain Diode Forward Voltage



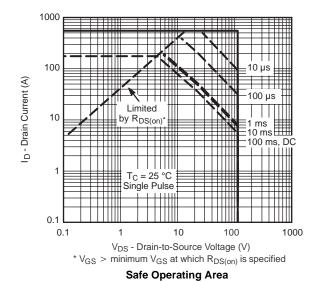
Drain Source Breakdown vs. Junction Temperature

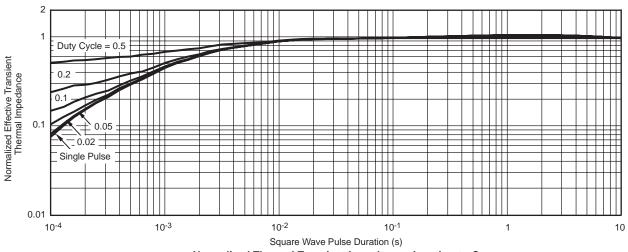


THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature





Normalized Thermal Transient Impedance, Junction-to-Case





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